

「KEK低速陽電子実験施設における陽電子回折研究およびPsビーム研究の新展開」
2012年10月3日(水)～4日(木)
KEK研究本館小林ホール

陽電子回折への期待

Expectation for positron diffractions

高橋敏男・白澤徹郎
(東大物性研)

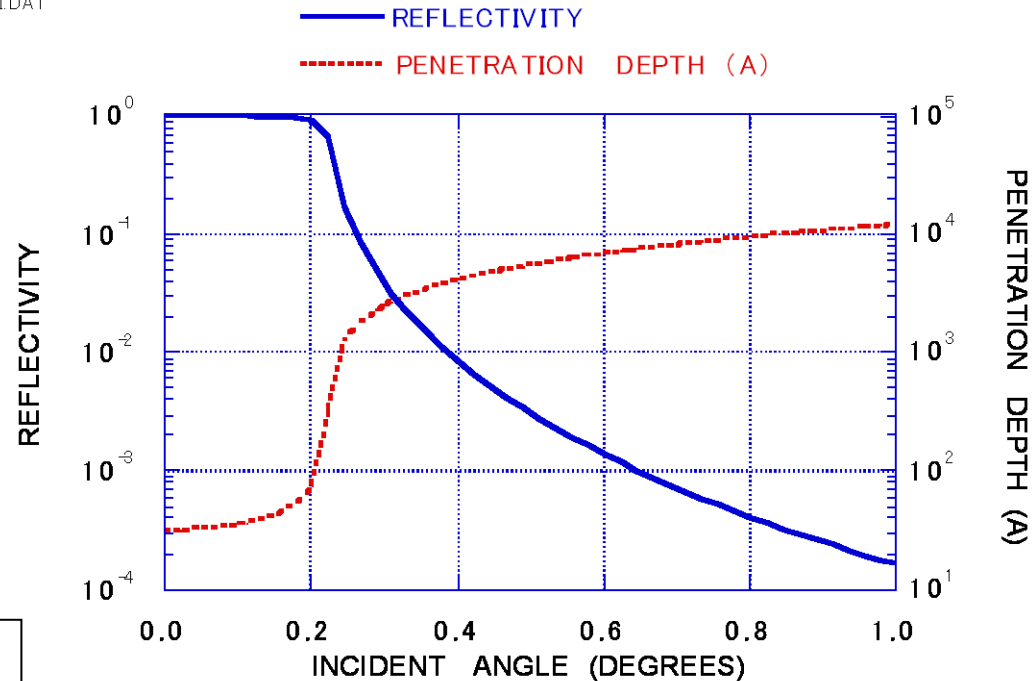
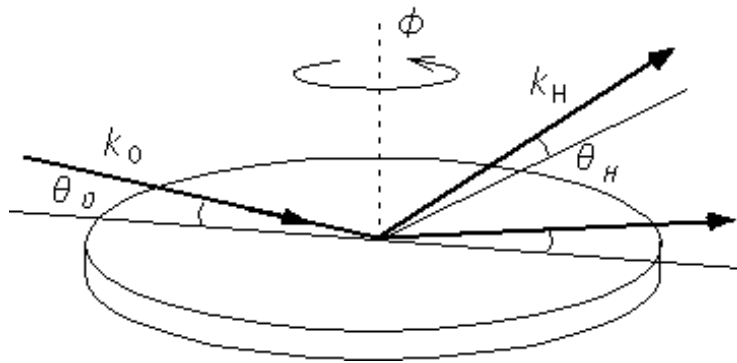
T. Takahashi, T. Shirasawa
(ISSP, Univ. of Tokyo)

outline

1. Surface X-ray diffraction
2. Difficult cases for SXD
 - large unit cell
 - deeply reconstructed structures
 - substrate with complicated structures
3. Experimental geometry
4. Analysis
 - holography
 - an example of SXD

Grazing incidence in-plane X-ray diffraction GIXD

P2.S1.DAT



全反射

X線の侵入深さ浅い
表面に敏感

散乱ベクトルが面内 : $Q_z (=L) = 0$
表面投影2次元構造

penetration depth:
more than 100 Å
1000 Å to 1 μm

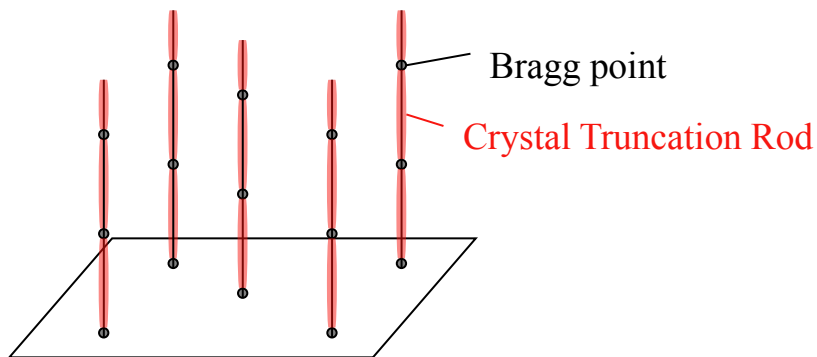
X-ray CTR scattering

CTR (Crystal Truncation Rod) scattering

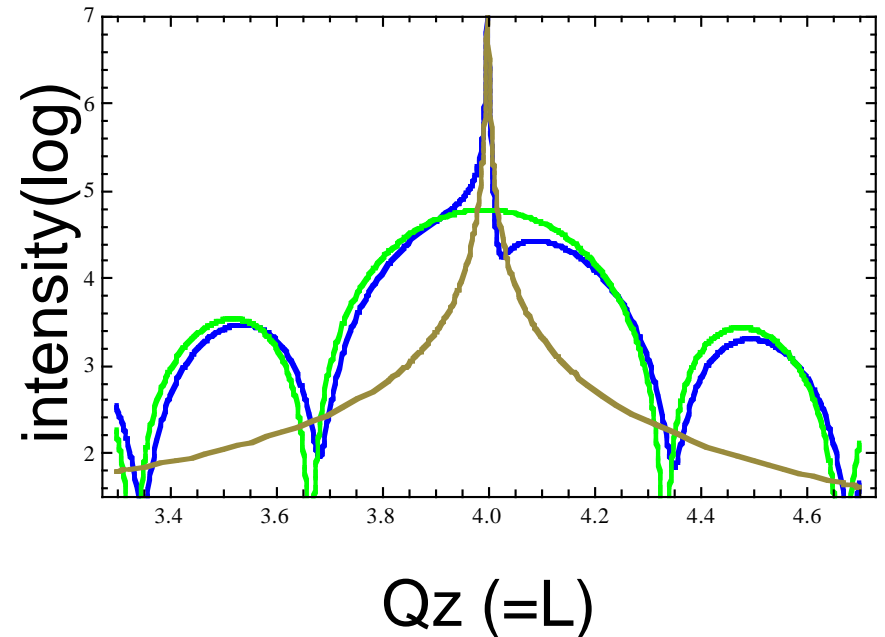
$$I(\mathbf{q}) \propto \left| F^{substrate}(\mathbf{q}) + e^{i\mathbf{q} \cdot \mathbf{h}} F^{overlayer}(\mathbf{q}) \right|^2$$

干涉項

\mathbf{h} : interfacial separation vector



原子レベルの表面・界面構造
薄膜内部構造

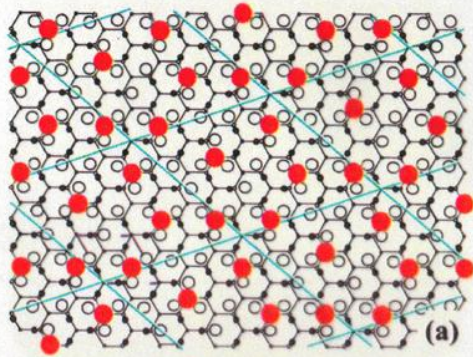


Surface Sensitivity in SXD

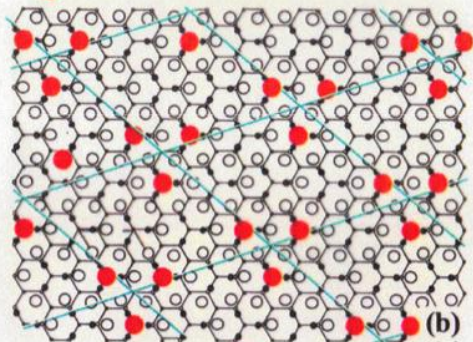
- Integral order rods
 - rod scan (CTR scattering, reflectivity)
 - in plane (GIXD)
 - 100 Å to micron meter
- Fractional order rods:
 - rod scan
 - in plane (GIXD)
 - all reconstructed layers

Si(111)- $\sqrt{21} \times \sqrt{21}$ -(Ag+Au)

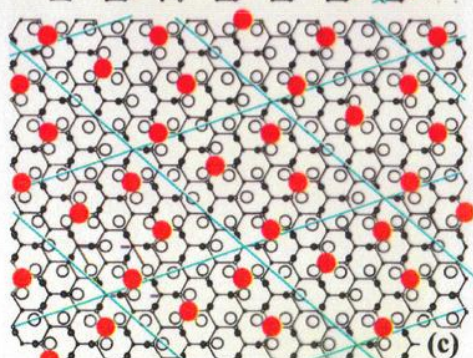
Au/Si(111)- $\sqrt{3} \times \sqrt{3}$ -Ag



A model proposed by Nogamni et al.



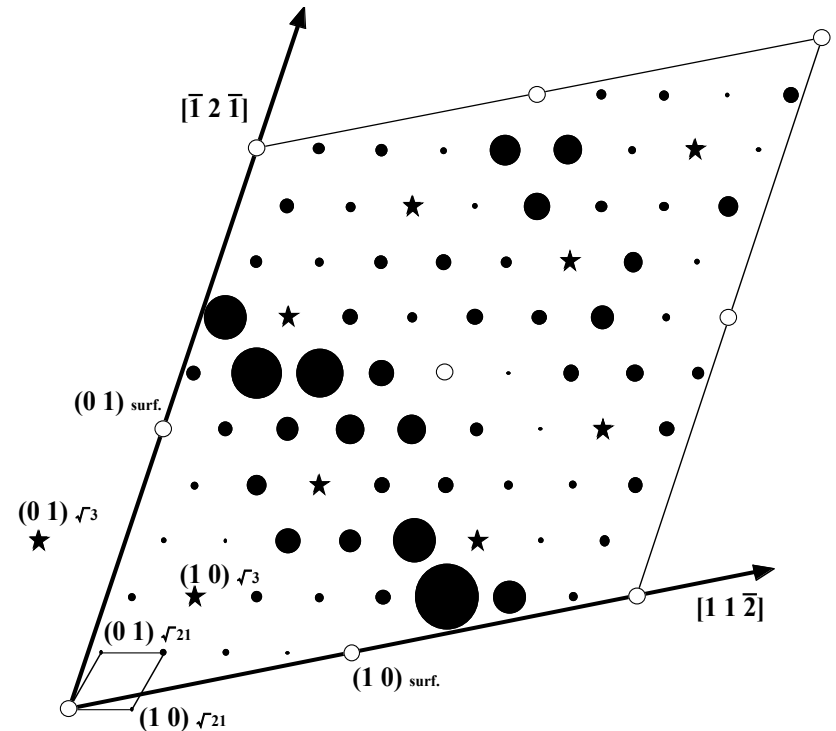
A model proposed by Ichimiya et al.



A model proposed by Tong et al.

... Si atoms ○ Ag atoms ● Au (or Ag) adatoms

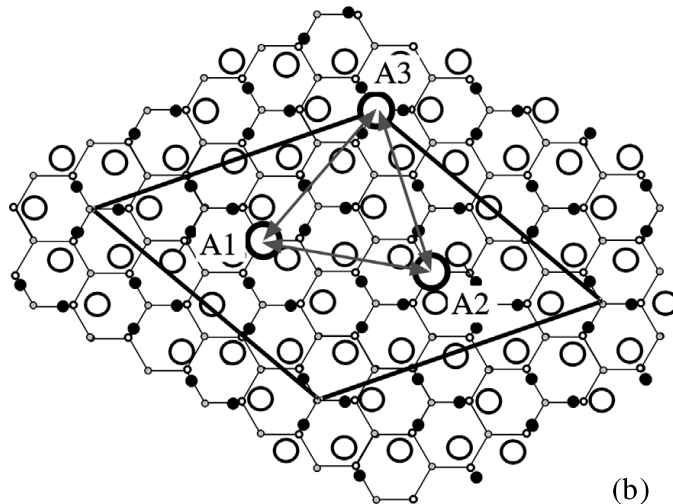
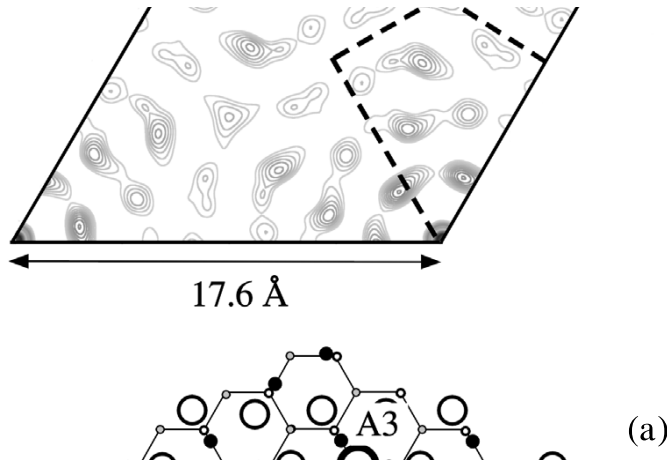
GIXD



Inequivalentな72点の逆格子を測定

- : 測定した逆格子点
(面積は積分強度に比例する)
- : 表面 1×1 の逆格子
- ★ : $\sqrt{3}$ 構造の逆格子

Patterson map



Ichimiya model

Tong model

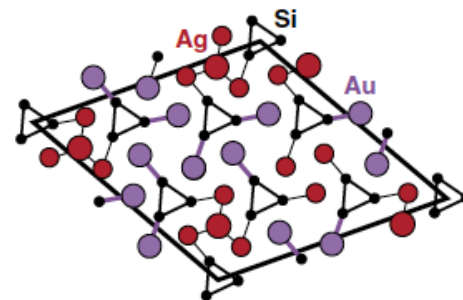
peak A: cannot explain by Au-Au

Nogami model

peak Aは説明できるが合わない

新しいモデルを提案したが、不十分
未解決

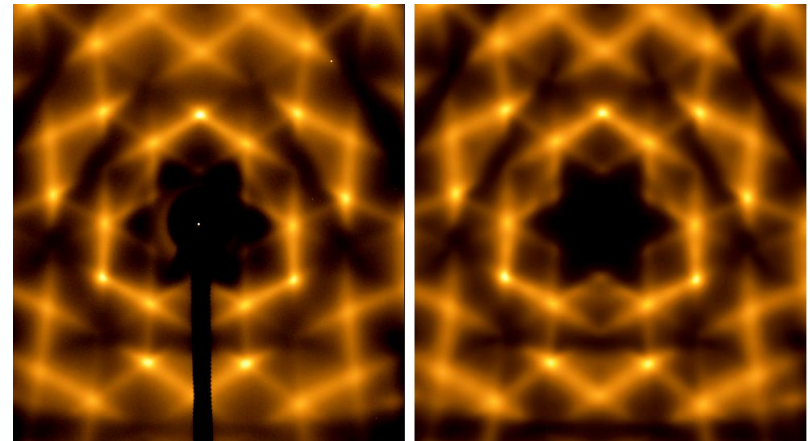
- Ag, Au: mixing (alloy)
- $\sqrt{3} \times \sqrt{3}$ -Ag (Si) layer(s):
 $\sqrt{21} \times \sqrt{21}$ -periodicity



Normal incidence geometry

- LEPD(LEED)
- Reflection geometry
- transmission X-ray diffraction
- TDS as a background
 - thin crystals

symmetry:
plane group



Si(111)

observed

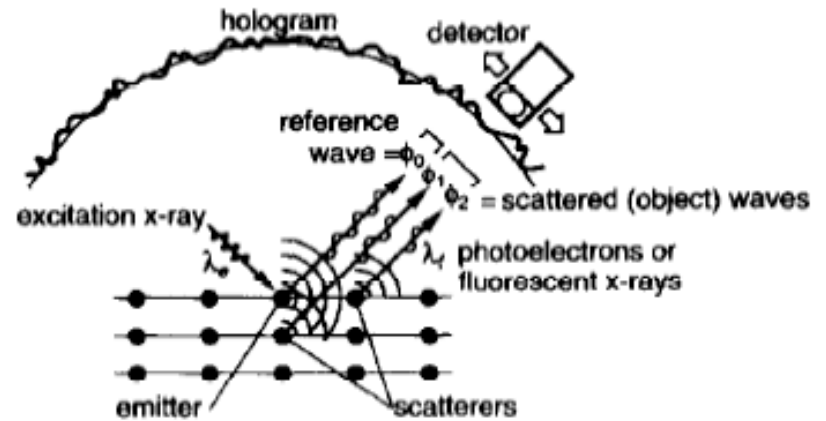
calculated

phonon dispersion

Holographic Methods

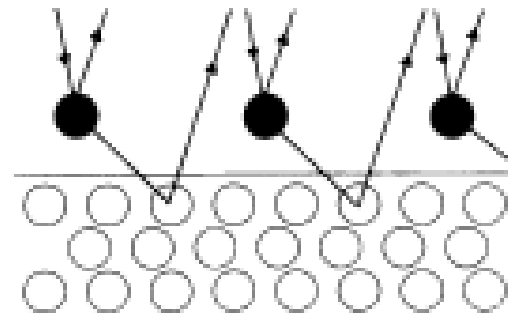
- Photoelectron holography
- X-ray fluorescence holography

(b) Photoelectron Holography (PH),
X-ray Fluorescence Holography (XFH)



C.S.Fadely et. al., PSS 54, 341(1997)

- LEED/LEPD holography

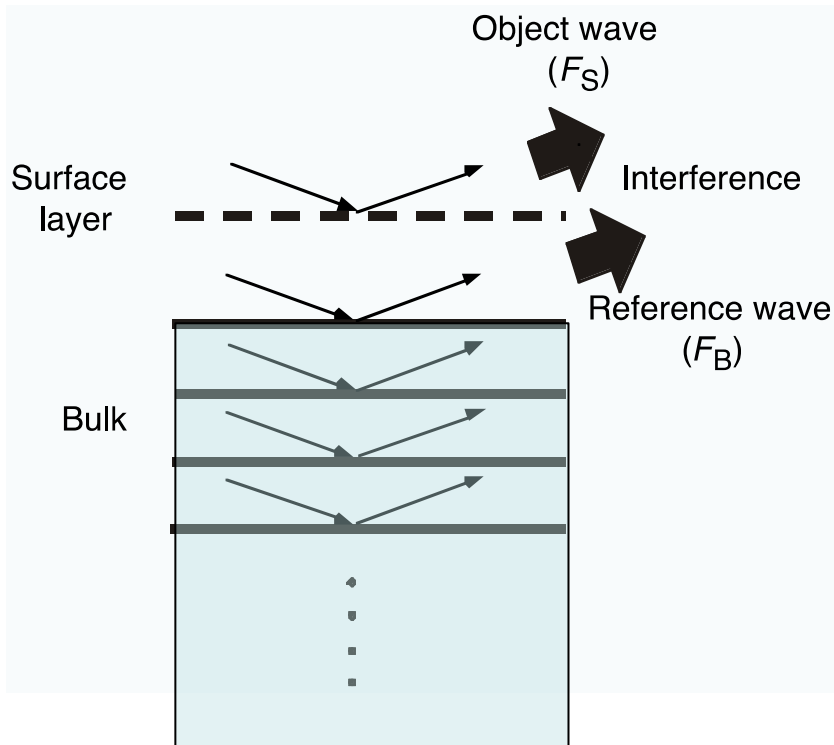


- CTR scattering holography

S.Y. Tong et. al., PRL 69, 3654(1991)

CTR scattering holography

CTR (Crystal truncation rod) scattering



表面構造 / 単結晶

$$I = | F_B + F_S |^2 = | R + O |^2$$

hologram

F_B : scattering amplitude by bulk

F_S : scattering amplitude by surface

$$F_B = \text{known}(\text{reference})$$

$$F_S = \text{unknown}(\text{object})$$

$$F_B = \sum_{n=1}^{\infty} F \exp(i2\pi n l)$$

$$= \frac{F}{1 - \exp(-i2\pi l)}$$

$$\mathbf{k} = h \mathbf{a}^* + k \mathbf{b}^* + l \mathbf{c}^*$$

scattering vector

CTR Holographic Method

Hologram function in SXD

$$\begin{aligned} \alpha(\mathbf{k}) &= \frac{I - I_0}{F_B^*} \\ &= \frac{F_B^* F_S + F_B F_S^* + |F_S|^2}{F_B^*} \\ &= F_S + \frac{F_B}{F_B^*} F_S^* + \frac{|F_S|^2}{F_B^*} \\ &= O + \frac{R}{R^*} O^* + \frac{|O|^2}{R^*} \end{aligned}$$

F_S : electron density

$I = |F_B + F_S|^2$: observed

$I_0 = |F_B|^2$: calculated

Reconstruction of atoms

$$U(\mathbf{r}) = \int_{h,k,l} \alpha(\mathbf{k}) \exp(-i 2\pi \mathbf{k} \cdot \mathbf{r}) d\mathbf{k}$$

$$O = F_S$$

O : atom image
electron density $\rho(\mathbf{r})$

O^* : twin atom

$$\text{Re}(U(\mathbf{r})) \rightarrow r(\mathbf{r})$$

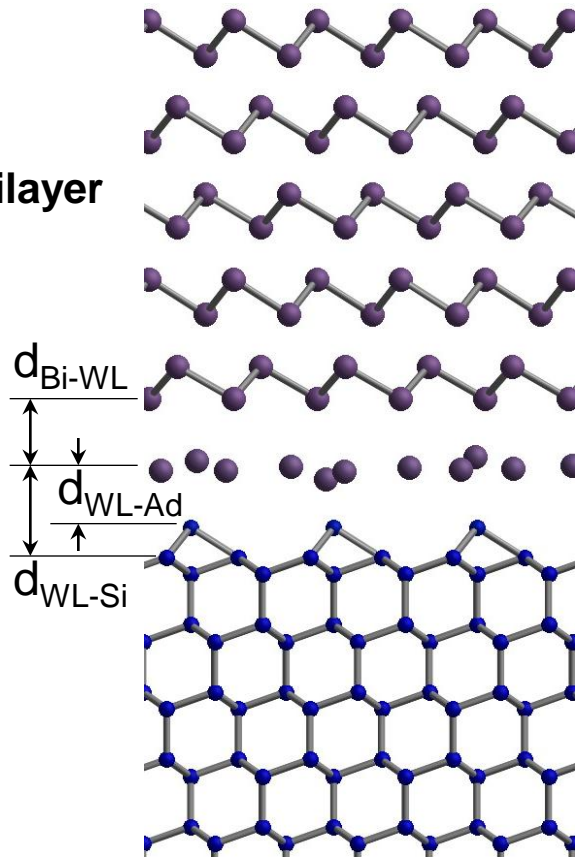
相互作用

Bi(001)-Wetting layer

Wetting layer-substrate

Bi

11-bilayer



side view

$$d_{\text{Bi-WL}} = 3.23 \text{ \AA}$$

Inter bilayer 距離 2.38 \AA

→ Bi(001)膜はfree standing
表面と界面層の構造もほぼ同じ

→ QWSのスピンの縮退を説明

$$d_{\text{WL-Adatp}} = 2.7 \text{ \AA}$$

共有結合半径和 = 2.59 \AA

Dalton Trans. 2832 (2008)

$$d_{\text{WL-Si}} = 4.12 \text{ \AA}$$

Van der Waals半径和 = 4.17 \AA

(J. Phys. Chem. A, 5806 (2009))



Si

BiはSi adatomとのみ相互作用
STM観察結果と一致

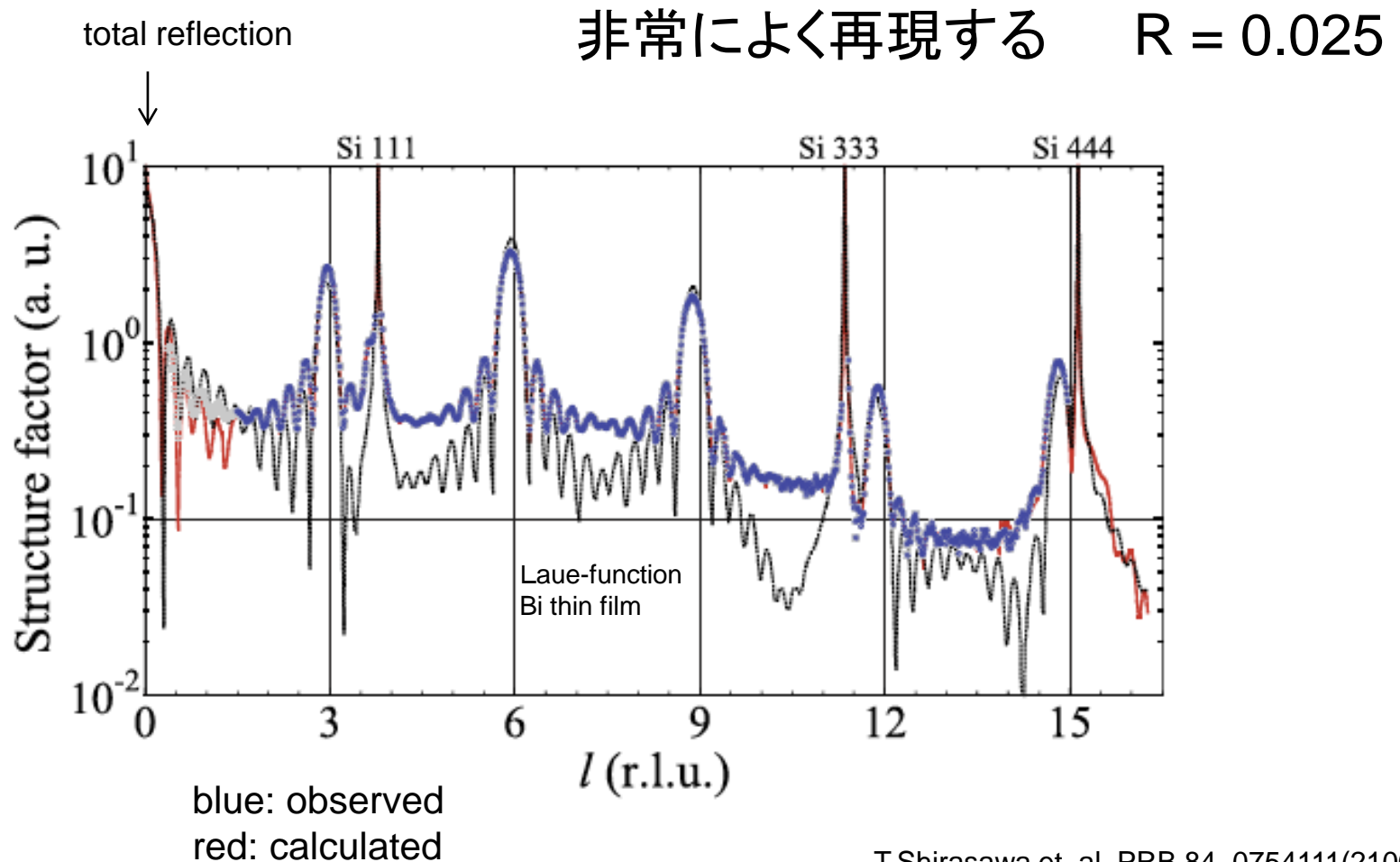
*J. Appl. Phys. 99, 014904 (2006).

Bi(001)/Si(111)-7x7

T.Shirasawa et. al, PRB 84. 0754111(2100)

電子密度分布から計算した構造因子

Holography + iterative phase retrieval method



Summary

Expectation for positron diffractions

1) Surface sensitivity

determination of topmost layer(s)

- Large unit cell
- deeply distorted structures
- substrate with complicated structure

2) Normal incidence condition

symmetry of surface structures

3) Development of analyses

depending on the degree of multiple scattering

- holographic method
- Patterson map
- iterative phase retrieval method(?)

Thank you!